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L Number	Hits	Search Text	DB	Time stamp
1	1672	118/719.ccls.	USPAT;	2004/01/09 20:14
			US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
2	2090	29/25.01.ccls.	USPAT;	2004/01/09 20:07
		,	US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
3	333	427/9.ccls.	USPAT;	2004/01/09 20:07
			US-PGPUB;	
			ЕРО; ЈРО;	
-			DERWENT;	
			IBM_TDB	******
4	6936	438/5-18.ccls.	USPAT;	2004/01/09 20:07
		,	US-PGPUB;	
			ЕРО; ЛРО;	
			DERWENT;	
_	2.422	500/10 40 50 00 104 100 111 110 101 102 I	IBM_TDB	2004/01/09 20:08
5	2423	700/19,49,52,99-104,108-111,119-121,123.ccls.	USPAT;	2004/01/09 20:08
			US-PGPUB;	
			ЕРО, ЛРО,	
			DERWENT; IBM_TDB	
	004	L1-L5	USPAT;	2004/01/09 20:08
6	894	L1-L3	US-PGPUB;	2004/01/09 20.08
			EPO; JPO;	
]			DERWENT;	
			IBM TDB	
7	13149	118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 20:08
'	13149	700/19,49,52,99-104,108-111,119-121,123.ccls.	US-PGPUB;	2004/01/07 20:00
		/////19,49,32,99-104,108-111,119-121,123.ccis.	ЕРО; ЛРО;	
			DERWENT;	
			IBM_TDB	
8	1237213	((semiconductor or (semi adj conductor) or semi-conductor or wafer or	USPAT;	2004/01/09 20:39
	1237213	IC or (integrated adj circuit) or lot or (micro adj electronic) or	US-PGPUB;	
		microelectronic or memory or (logic adj unit) or microprocessor) with	ЕРО; ЈРО;	
		(process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or making))	DERWENT;	
		(Francisco de Francisco de Fran	IBM_TDB	
9	7683	(118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPĀT;	2004/01/09 20:40
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	US-PGPUB;	
		or (semi adj conductor) or semi-conductor or wafer or IC or (integrated	ЕРО; ЛРО;	
		adj circuit) or lot or (micro adj electronic) or microelectronic or memory	DERWENT;	•
		or (logic adj unit) or microprocessor) with (process\$3 or fabricat\$3 or	IBM_TDB	
		produc\$4 or manufactur\$3 or making)))		
10	1146265	((semiconductor or (semi adj conductor) or semi-conductor or wafer or	USPAT;	2004/01/09 20:41
		IC or (integrated adj circuit) or lot or (micro adj electronic) or	US-PGPUB;	
		microelectronic or memory or (logic adj unit) or microprocessor or	ЕРО; ЈРО;	
		process\$3 or fabricat\$3 or produc\$4 or manufactur\$3) with (deposit\$3	DERWENT;	
		or etch\$3 or metrology or measur\$3 or tool\$3))	IBM_TDB	
11	5313	((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 20:16
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	US-PGPUB;	
		or (semi adj conductor) or semi-conductor or wafer or IC or (integrated	EPO; JPO;	
		adj circuit) or lot or (micro adj electronic) or microelectronic or memory	DERWENT;	
		or (logic adj unit) or microprocessor) with (process\$3 or fabricat\$3 or	IBM_TDB	
		produc\$4 or manufactur\$3 or making)))) and (((semiconductor or (semi		
		adj conductor) or semi-conductor or wafer or IC or (integrated adj		
		circuit) or lot or (micro adj electronic) or microelectronic or memory or	1	
		(logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4		
		or manufactur\$3) with (deposit\$3 or etch\$3 or metrology or measur\$3 or	1	
l	<u> </u>	tool\$3)))	1	L

12	1860420	((semiconductor or (semi adj conductor) or semi-conductor or wafer or	USPAT;	2004/01/09 20:44
12	1800420	IC or (integrated adj circuit) or lot or (micro adj electronic) or	US-PGPUB;	2004/01/09 20.44
		microelectronic or memory or (logic adj unit) or microprocessor or	ЕРО; ЈРО;	
		process\$3 or fabricat\$3 or produc\$4 or manufactur\$3 or deposit\$3 or	DERWENT;	
		etch\$3 or metrology or measur\$3 or tool\$3) with (((process\$3 or cycle or	IBM_TDB	
		average or mean) near3 (time or rate)) or uniform\$3 or thickness or		
		(critical adj dimension\$3) or CD or variability or target or accura\$4 or		
1.2	4526	defect\$5))	USPAT;	2004/01/09 20:23
13	4320	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	US-PGPUB;	2004/01/09 20.23
		or (semi adj conductor) or semi-conductor or wafer or IC or (integrated	EPO; JPO;	
		adj circuit) or lot or (micro adj electronic) or microelectronic or memory	DERWENT;	
Ì		or (logic adj unit) or microprocessor) with (process\$3 or fabricat\$3 or	IBM_TDB	
		produc\$4 or manufactur\$3 or making)))) and (((semiconductor or (semi		
		adj conductor) or semi-conductor or wafer or IC or (integrated adj		
		circuit) or lot or (micro adj electronic) or microelectronic or memory or		
		(logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4		
		or manufactur\$3) with (deposit\$3 or etch\$3 or metrology or measur\$3 or		
		tool\$3)))) and (((semiconductor or (semi adj conductor) or		
		semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro		
		adj electronic) or microelectronic or memory or (logic adj unit) or		
		microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3		
		or deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3) with		
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or		
		uniform\$3 or thickness or (critical adj dimension\$3) or CD or variability or target or accura\$4 or defect\$5)))		
14	1069	700/19,49,52,99-104,108-111,119-121,123.ccls. and ((((118/719.ccls. or	USPAT;	2004/01/09 20:23
* '		29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	US-PGPUB;	200
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	ЕРО; ЛРО;	
		or (semi adj conductor) or semi-conductor or wafer or IC or (integrated	DERWENT;	
1		adj circuit) or lot or (micro adj electronic) or microelectronic or memory	IBM_TDB	
1		or (logic adj unit) or microprocessor) with (process\$3 or fabricat\$3 or		
		produc\$4 or manufactur\$3 or making)))) and (((semiconductor or (semi		
		adj conductor) or semi-conductor or wafer or IC or (integrated adj		
		circuit) or lot or (micro adj electronic) or microelectronic or memory or		
		(logic adj unit) or microprocessor or process\$3 or fabricat\$3 or produc\$4		
		or manufactur\$3) with (deposit\$3 or etch\$3 or metrology or measur\$3 or		
		tool\$3)))) and (((semiconductor or (semi adj conductor) or		
		semi-conductor or wafer or IC or (integrated adj circuit) or lot or (micro adj electronic) or microelectronic or memory or (logic adj unit) or		
		microprocessor or process\$3 or fabricat\$3 or produc\$4 or manufactur\$3		
		or deposit\$3 or etch\$3 or metrology or measur\$3 or tool\$3) with		
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or		
		uniform\$3 or thickness or (critical adj dimension\$3) or CD or variability		
		or target or accura\$4 or defect\$5))))		•
15	560847	((semiconductor or (semi adj conductor) or semi-conductor or wafer)	USPAT;	2004/01/09 20:40
	·	with (process\$3 or fabricat\$3 or production or manufactur\$3))	US-PGPUB;	_
ŀ			ЕРО; ЛРО;	
	1		DERWENT;	
1,6		(110/710 -1 - 20/05 01 -1 - 427/0 -1 - 422/7 12 -1	IBM_TDB	2004/01/00 20 40
16	6256	(118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or 700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	USPAT; US-PGPUB;	2004/01/09 20:40
		or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or	оз-гогов, ЕРО; JРО;	
		fabricat\$3 or production or manufactur\$3)))	DERWENT;	
		and the state of t	IBM TDB	
17	2140	((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 20:50
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	US-PGPUB;	
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		fabricat\$3 or production or manufactur\$3)))) and ((tool\$3 or chamber or	DERWENT;	
	1	processor) with (deposit\$3 or etch\$3 or metrology or measur\$3 or	IBM_TDB	
		polish\$3 or lithography or exposure or oxidation or oxidizing or		
	1	implant\$5 or planariz\$5 or CVD or vapor-deposit\$3 or chemical-vapor		
L	L	or clean\$3))		

18	873	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 21:03
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	US-PGPUB;	
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		fabricat\$3 or production or manufactur\$3)))) and ((tool\$3 or chamber or	DERWENT;	
		processor) with (deposit\$3 or etch\$3 or metrology or measur\$3 or	IBM_TDB	
		polish\$3 or lithography or exposure or oxidation or oxidizing or		
		implant\$5 or planariz\$5 or CVD or vapor-deposit\$3 or chemical-vapor		
		or clean\$3))) and (chamber with (((process\$3 or cycle or average or		
		mean) near3 (time or rate)) or uniform\$3 or thickness or (critical adj		
		dimension\$3) or CD or variability or target or accura\$4 or defect\$5))		
19	113	700/19,49,52,99-104,108-111,119-121,123.ccls. and ((((118/719.ccls. or	USPAT;	2004/01/09 20:45
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	1	700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	ЕРО; ЈРО;	
		or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or	DERWENT;	
		fabricat\$3 or production or manufactur\$3)))) and ((tool\$3 or chamber or	IBM_TDB	
		processor) with (deposit\$3 or etch\$3 or metrology or measur\$3 or		
		polish\$3 or lithography or exposure or oxidation or oxidizing or		
		implant\$5 or planariz\$5 or CVD or vapor-deposit\$3 or chemical-vapor		
		or clean\$3))) and (chamber with (((process\$3 or cycle or average or		
		mean) near3 (time or rate)) or uniform\$3 or thickness or (critical adj		
		dimension\$3) or CD or variability or target or accura\$4 or defect\$5)))		
20	1804	((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 20:50
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	US-PGPUB;	
		or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or	ЕРО; ЛРО;	
		fabricat\$3 or production or manufactur\$3)))) and ((tool\$3 or chamber or	DERWENT;	
	:	processor) with (deposit\$3 or etch\$3 or metrology or measur\$3))	IBM_TDB	
21	581	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 20:51
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	US-PGPUB;	
		or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or	ЕРО; ЈРО;	
		fabricat\$3 or production or manufactur\$3)))) and ((tool\$3 or chamber or	DERWENT;	
	. [processor) with (deposit\$3 or etch\$3 or metrology or measur\$3))) and	IBM_TDB	
		(chamber near5 (((process\$3 or cycle or average or mean) near3 (time or		
		rate)) or uniform\$3 or thickness or (critical adj dimension\$3) or CD or		
		variability or target or accura\$4 or defect\$5))		-
22	263	((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 21:10
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	US-PGPUB;	
		or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or	ЕРО; ЈРО;	
*		fabricat\$3 or production or manufactur\$3)))) and ((tool\$3 or chamber or	DERWENT;	
		processor) with (deposit\$3 or etch\$3 or metrology or measur\$3))) and	IBM_TDB	
		(chamber near5 (((process\$3 or cycle or average or mean) near3 (time or		
		rate)) or uniform\$3 or thickness or (critical adj dimension\$3) or CD or		
		variability or target or accura\$4 or defect\$5))) and (@pd<=20000813)		
23	439	((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 21:37
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	US-PGPUB;	
	, ,	or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or	ЕРО; ЛРО;	
		fabricat\$3 or production or manufactur\$3)))) and (chamber with	DERWENT;	
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		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or		
•		(critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or		
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		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	US-PGPUB;	
		or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or	ЕРО; ЛРО;	
		fabricat\$3 or production or manufactur\$3)))) and (chamber with	DERWENT;	
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or	IBM_TDB	
		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or		
		(critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or		
		precision) near3 process\$3)))) and (@pd<=20000813)	L	

25	23	(((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 21:34
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		fabricat\$3 or production or manufactur\$3)))) and (chamber with	DERWENT;	
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or	IBM_TDB	
		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or		
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26	272	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 21:34
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	US-PGPUB;	
		or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or	ЕРО; ЈРО;	
		fabricat\$3 or production or manufactur\$3)))) and (chamber with	DERWENT;	•
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or	IBM_TDB	
		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or		
	1	(critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or		
] .	precision) near3 process\$3)))) not ((((118/719.ccls. or 29/25.01.ccls. or		
		427/9.ccls. or 438/5-18.ccls. or		
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or		
	·			
		fabricat\$3 or production or manufactur\$3)))) and (chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or		
		(((process\$5 of cycle of average of mean) hears (time of fate)) of (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or		
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27	55	((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 21:37
21	33	700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor	US-PGPUB;	200 1101105 21.57
		or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or	ЕРО; ЛРО;	
		fabricat\$3 or production or manufactur\$3)))) and (chamber with	DERWENT;	
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or	IBM_TDB	
		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or		
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		precision) near3 process\$3)))) not ((((118/719.ccls. or 29/25.01.ccls. or		
		427/9.ccls. or 438/5-18.ccls. or		
	1	700/19,49,52,99-104,108-111,119-121,123.ccls.) and (((semiconductor		
		or (semi adj conductor) or semi-conductor or wafer) with (process\$3 or		
		fabricat\$3 or production or manufactur\$3)))) and (chamber with		
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or		
		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or		
	ļ	(critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or		
		precision) near3 process\$3)))) and (@pd<=20000813))) and (applied adj		
	1	materials).as.		
28	513	(118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 21:51
		700/19,49,52,99-104,108-111,119-121,123 ccls.) and (chamber with	US-PGPUB;	
	ļ.	(((process\$3 or cycle or average or mean) near3 (time or rate)) or	ЕРО; ЈРО;	
		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or	DERWENT;	
		(critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or	IBM_TDB	
		precision) near3 process\$3)))		
29	78	((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 21:37
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with	US-PGPUB;	
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or	ЕРО; ЈРО;	
		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or	DERWENT;	
		(critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or	IBM_TDB	
20		precision) near3 process\$3)))) and (applied adj materials).as.	I IODAT.	2004/01/00 21:27
30	23	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 21:37
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with	US-PGPUB;	
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or	EPO; JPO;	
		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or	DERWENT;	
			IDIM I DD	
	•	(critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or precision) near3 process\$3)))) and (applied adj materials).as.) and (@pd<=20000813)	IBM_TDB	

21	55	(((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 21:38
31	33	700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with	US-PGPUB;	2004/01/09 21:38
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or	ЕРО; ЈРО;	
-		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or	DERWENT;	
		(critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or	IBM_TDB	
		precision) near3 process\$3)))) and (applied adj materials).as.) not		
		((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or		
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with		
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or		
		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or		
		(critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or		
		precision) near3 process\$3)))) and (applied adj materials).as.) and		
32	55	(@pd<=20000813)) ((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 22:23
32	33	700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with	US-PGPUB;	2004/01/09 22:23
		((((process\$3 or cycle or average or mean) near3 (time or rate)) or	EPO; JPO;	
		((c) recessor of cycle of average of mean) hears (time of face) of (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or	DERWENT;	
		(critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or	IBM_TDB	•
		precision) near3 process\$3)))) and (applied adj materials).as.) not		
		(((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or		
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with		
	1	(((process\$3 or cycle or average or mean) near3 (time or rate)) or		
		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or		
		(critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or		
		precision) near3 process\$3)))) and (applied adj materials) as.) and		
	1	(@pd<=20000813))) and (chamber with (((process\$3 or cycle or average		
		or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target		
		or value)) or ((accura\$4 or precision) near3 process\$3))).clm		
33	12	(((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 21:52
)))	12	700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with	US-PGPUB;	200-1/01/07 21:32
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or	EPO; JPO;	
		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or	DERWENT;	
		(critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or	IBM_TDB	
		precision) near3 process\$3)))) and (applied adj materials).as.) not	_	
		(((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or		
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with		
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or		
		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or		
		(critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or		
		precision) near3 process\$3)))) and (applied adj materials).as.) and (@pd<=20000813))) and (chamber with (((process\$3 or cycle or average		
		or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or		
		variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target		_
		or value)) or ((accura\$4 or precision) near3 process\$3))).clm.		•
38	55	(((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	USPAT;	2004/01/09 22:24
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with	US-PGPUB;	
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or	ЕРО; ЈРО;	
		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or	DERWENT;	
		(critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or	IBM_TDB	
		precision) near3 process\$3)))) and (applied adj materials).as.) not		
		((((118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or		
		700/19,49,52,99-104,108-111,119-121,123.ccls.) and (chamber with		
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or		•
		(critical adj dimension\$3) or CD or target or value)) or ((accura\$4 or		
		precision) near3 process\$3)))) and (applied adj materials).as.) and		
		(@pd<=20000813))) and (chamber with (((process\$3 or cycle or average		
		or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or		
		variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target		
		or value or parameter)) or ((accura\$4) near3 (process\$3 or tool or		
]	chamber)))).clm		

39	1582	(chamber with (((process\$3 or cycle or average or mean) near3 (time or	USPAT;	2004/01/09 22:28
		rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3	US-PGPUB;	1
		(thickness or (critical adj dimension\$3) or CD or target or value or	ЕРО; ЛРО;	
		parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber)))).clm.	DERWENT;	
	_,	(1) 1 (1) (1) (2)	IBM_TDB	2004/01/00 22:21
40	74	((chamber with (((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3	USPAT; US-PGPUB;	2004/01/09 22:31
	į į	(thickness or (critical adj dimension\$3) or CD or target or value or	EPO; JPO;	
		parameter)) or ((accura\$4) near3 (process\$3 or tool or chamber)))).clm.)	DERWENT;	
	į į	and (118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	IBM_TDB	
	į į	700/19,49,52,99-104,108-111,119-121,123.ccls.)	1.5.1.1_1.5.2	
41	54	(chamber with (determin\$5 or comput\$5 or calculat\$3) with	USPAT;	2004/01/09 22:31
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or	US-PGPUB;	
		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or	ЕРО; ЈРО;	
		(critical adj dimension\$3) or CD or target or value or parameter)) or	DERWENT;	
		((accura\$4) near3 (process\$3 or tool or chamber)))).clm. and software	IBM_TDB	
42	18	((chamber with (determin\$5 or comput\$5 or calculat\$3) with	USPAT;	2004/01/09 22:31
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or	US-PGPUB;	
		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or	ЕРО; ЛРО;	
		(critical adj dimension\$3) or CD or target or value or parameter)) or	DERWENT;	
		((accura\$4) near3 (process\$3 or tool or chamber)))).clm. and software)	IBM_TDB	
		and (118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or		
43	153	700/19,49,52,99-104,108-111,119-121,123.ccls.) (chamber with (determin\$5 or comput\$5 or calculat\$3) with	USPAT;	2004/01/09 22:31
43	155	(((process\$3 or cycle or average or mean) near3 (time or rate)) or	US-PGPUB;	2004/01/07 22.31
		((threess of eyele of average of mean) nears (time of rate)) of (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or	EPO; JPO;	
	'	(critical adj dimension\$3) or CD or target or value or parameter)) or	DERWENT;	
		((accura\$4) near3 (process\$3 or tool or chamber)))).clm.	IBM_TDB	
45	36	((chamber with (determin\$5 or comput\$5 or calculat\$3) with	USPAT;	2004/01/09 22:32
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or	US-PGPUB;	
	,	(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or	ЕРО; ЈРО;	
		(critical adj dimension\$3) or CD or target or value or parameter)) or	DERWENT;	
		((accura\$4) near3 (process\$3 or tool or chamber)))).clm. and software)	IBM_TDB	
		not (((chamber with (determin\$5 or comput\$5 or calculat\$3) with		
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or		
		(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3) or CD or target or value or parameter)) or		
		((accura\$4) near3 (process\$3 or tool or chamber)))).clm. and software)		
		and (118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or	·	
		700/19,49,52,99-104,108-111,119-121,123.ccls.))		
44	25	((chamber with (determin\$5 or comput\$5 or calculat\$3) with	USPAT;	2004/01/09 22:46
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or	US-PGPUB;	
	İ	(defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or	ЕРО; ЛРО;	·
		(critical adj dimension\$3) or CD or target or value or parameter)) or	DERWENT;	•
		((accura\$4) near3 (process\$3 or tool or chamber)))).clm.) and	IBM_TDB	
		(118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or		
46	_	700/19,49,52,99-104,108-111,119-121,123.ccls.)	USPAT;	2004/01/09 22:46
46	7	(((chamber with (determin\$5 or comput\$5 or calculat\$3) with	US-PGPUB;	2004/01/09 22.40
		(((process\$3 or cycle or average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or ((uniform\$3 or variab\$5) near3 (thickness or	EPO; JPO;	
		(critical adj dimension\$3) or CD or target or value or parameter)) or	DERWENT;	
		((accura\$4) near3 (process\$3 or tool or chamber)))).clm.) and	IBM_TDB	
		(118/719.ccls. or 29/25.01.ccls. or 427/9.ccls. or 438/5-18.ccls. or		
		700/19,49,52,99-104,108-111,119-121,123.ccls.)) not ((chamber with		
		(determin\$5 or comput\$5 or calculat\$3) with (((process\$3 or cycle or		
		average or mean) near3 (time or rate)) or (defect\$5 near3 rate) or		
		((uniform\$3 or variab\$5) near3 (thickness or (critical adj dimension\$3)		
		or CD or target or value or parameter)) or ((accura\$4) near3 (process\$3		
		or tool or chamber)))).clm. and software)		
-	2	20030029383.pn.	USPAT;	2004/01/09 20:06
	-		US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
	<u> </u>		םמו ואים	<u> </u>